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(54) **ORGANIC LIGHT EMITTING DIODE
DISPLAY DEVICE**

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See application file for complete search history.

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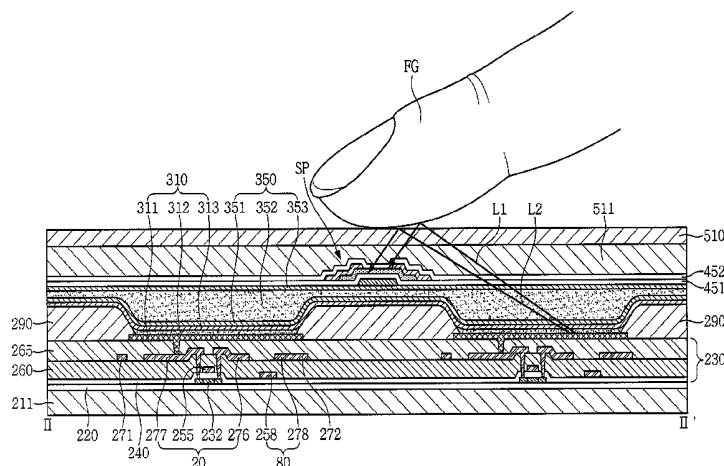
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(57) **ABSTRACT**

An organic light emitting diode display device includes a substrate, a plurality of organic light emitting diodes on the substrate, a thin film encapsulation layer on the organic light emitting diodes, and at least one sensor on the thin film encapsulation layer, the sensor including a sensing gate electrode, an oxide semiconductor layer overlapping the sensing gate electrode, a sensing source electrode connected to the oxide semiconductor layer, and a sensing drain electrode spaced apart from the sensing source electrode and connected to the oxide semiconductor layer.

20 Claims, 11 Drawing Sheets



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G09G 2310/0262 (2013.01); *G09G 2354/00*
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FIG. 1

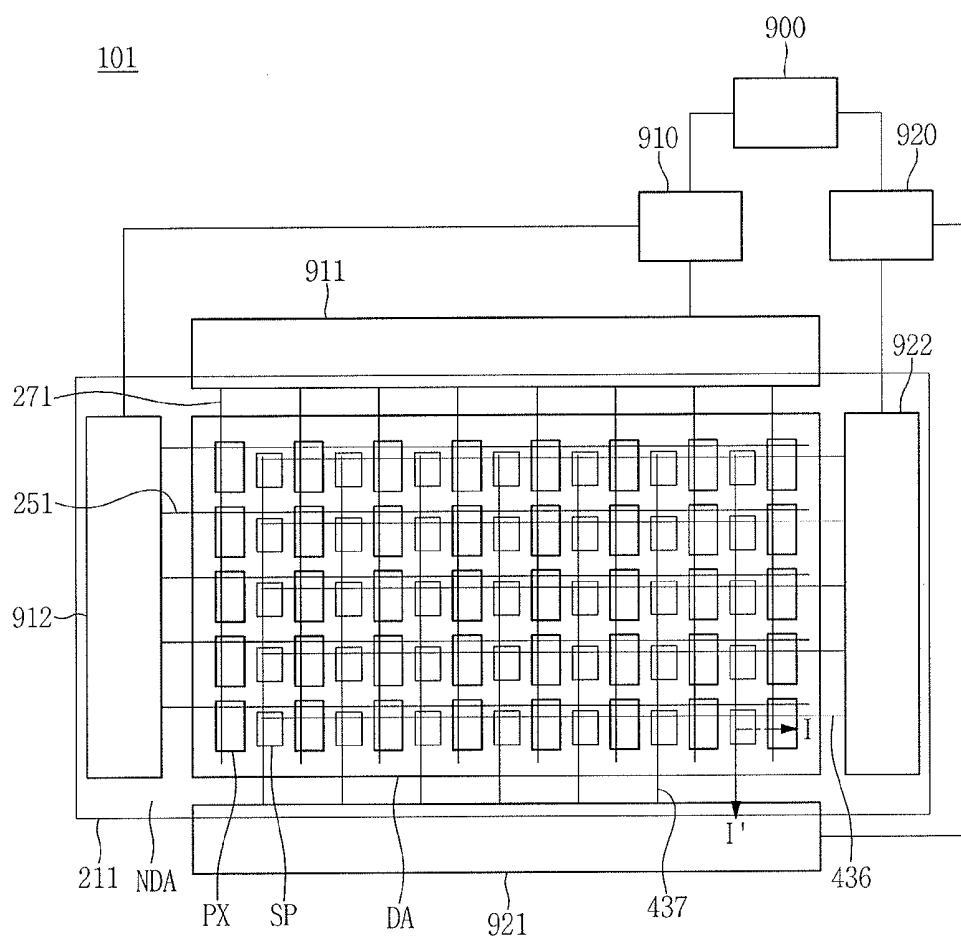


FIG. 2

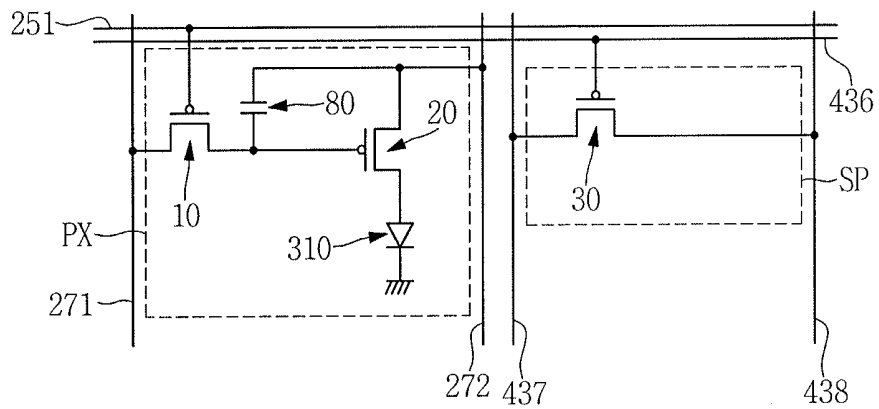


FIG. 3

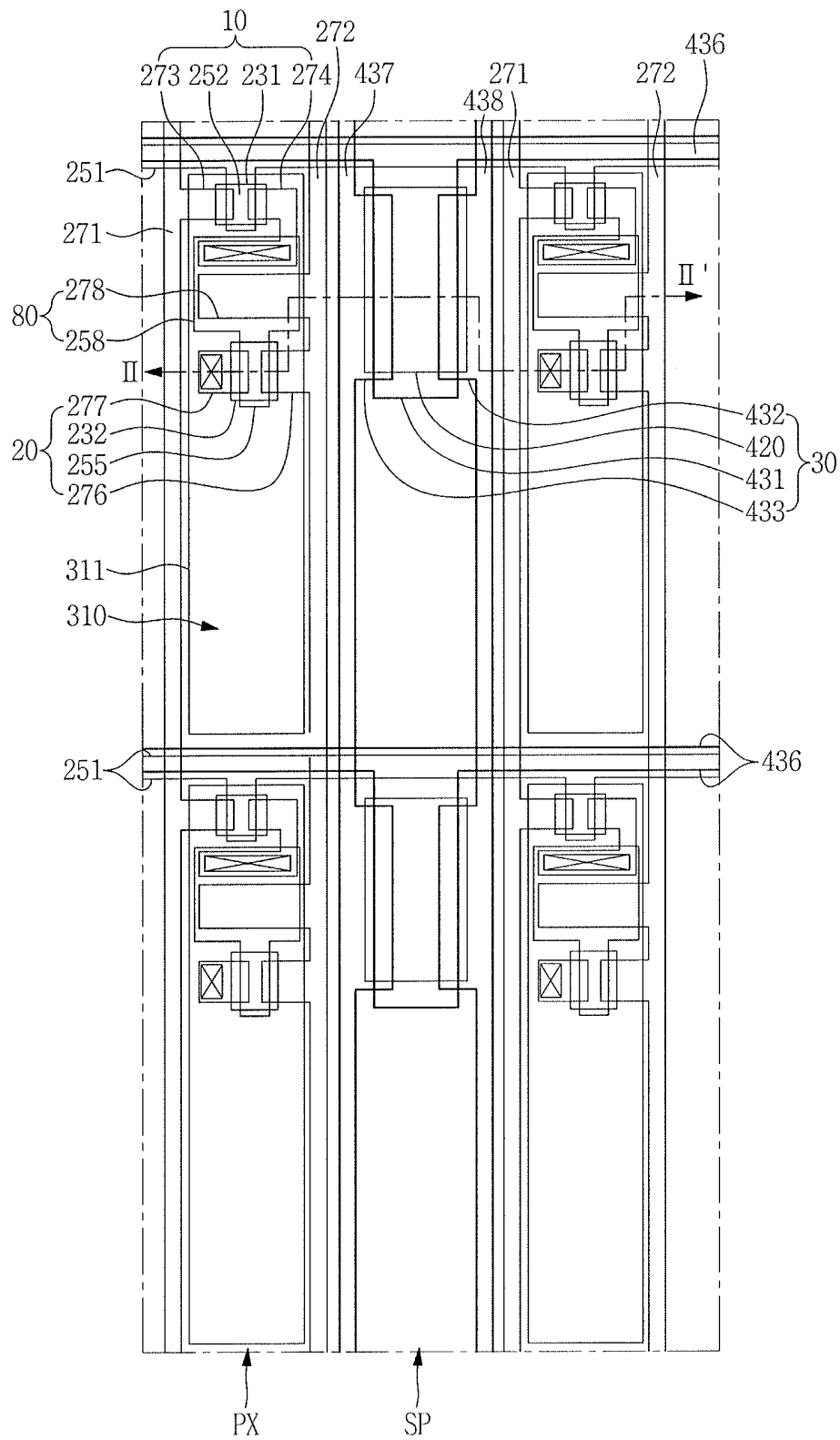


FIG. 4

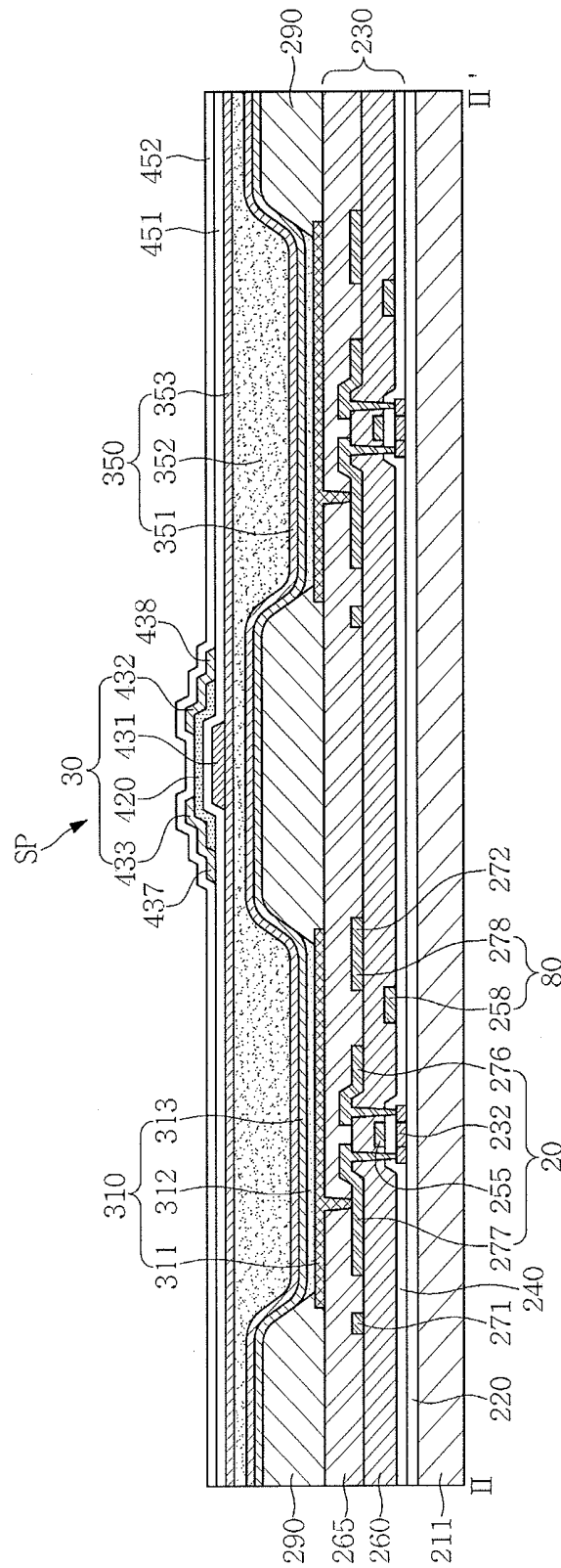


FIG. 5

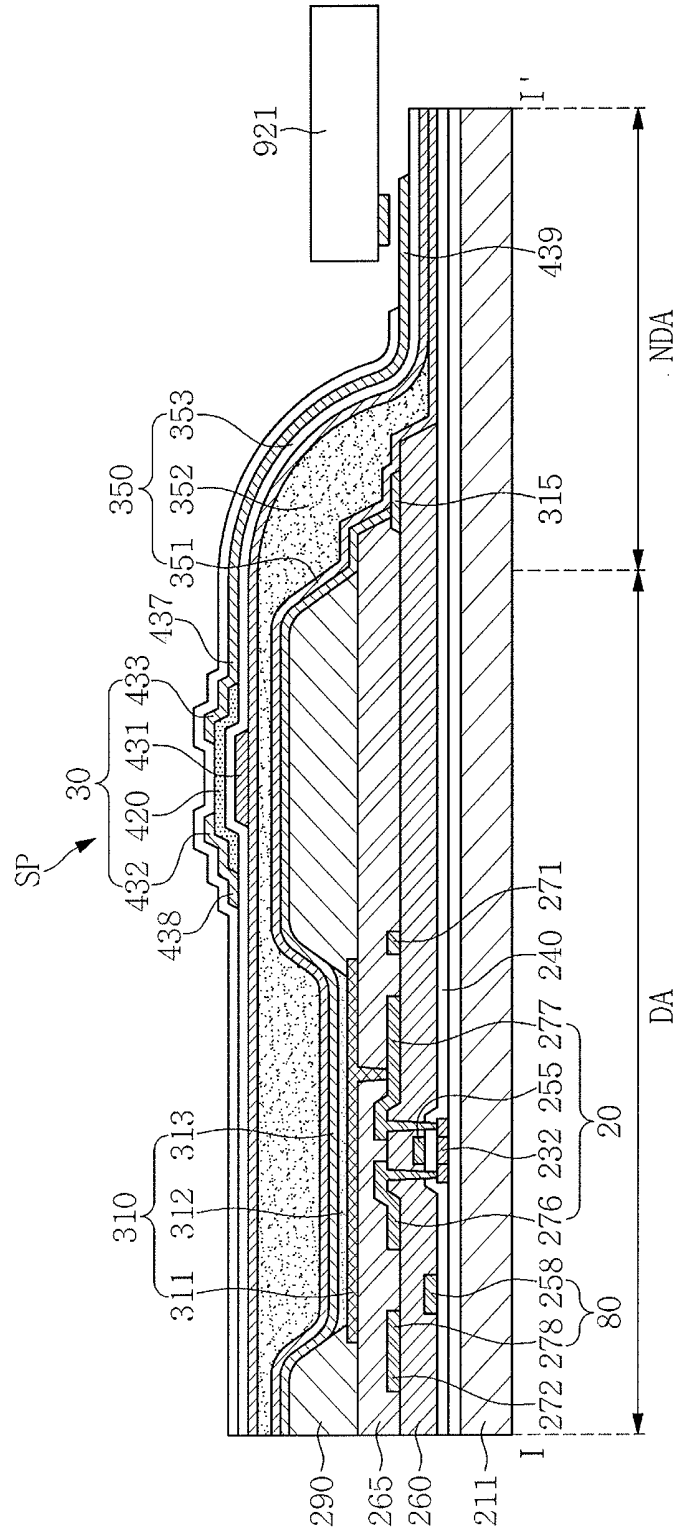


FIG. 7

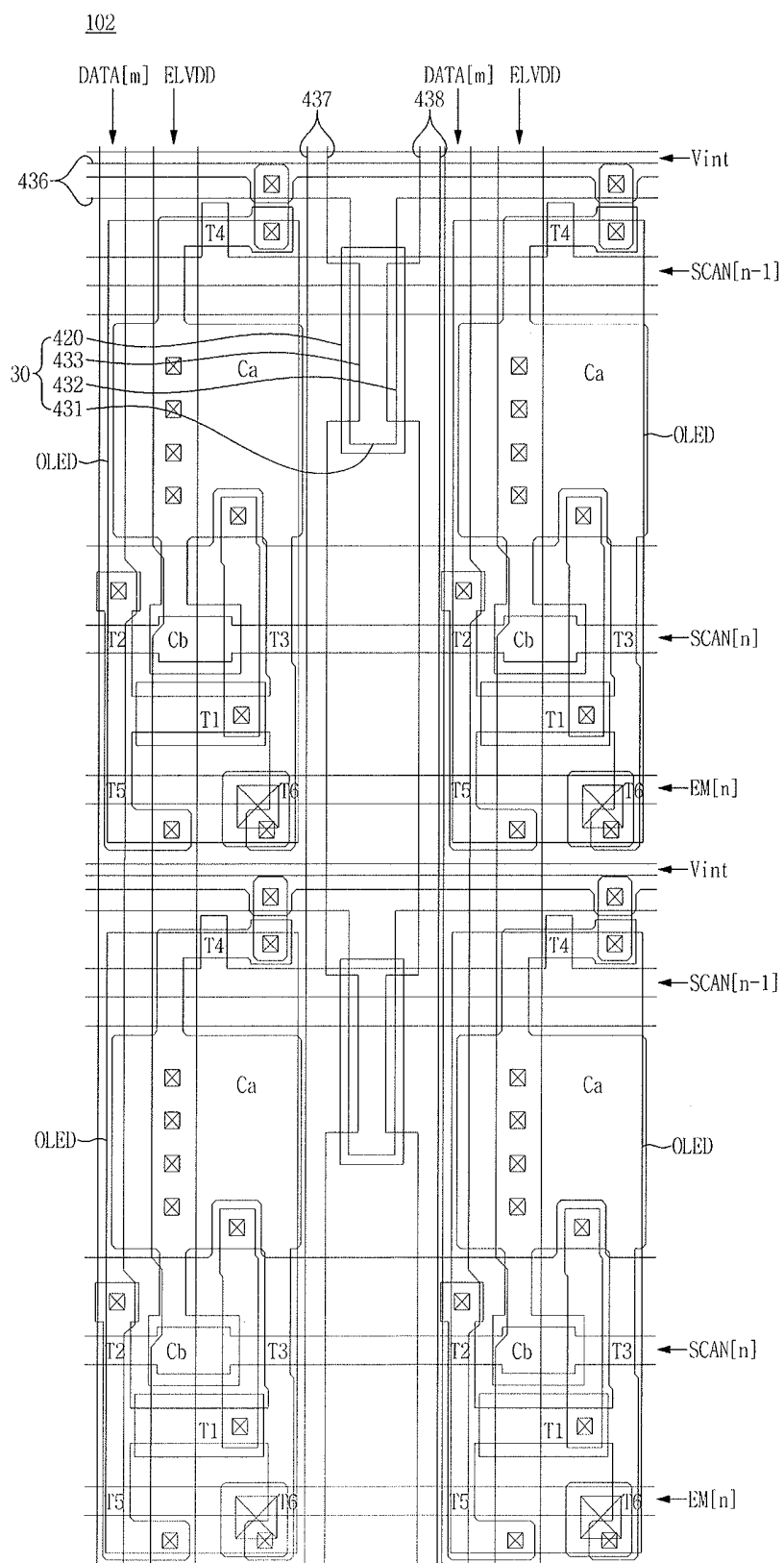


FIG. 8

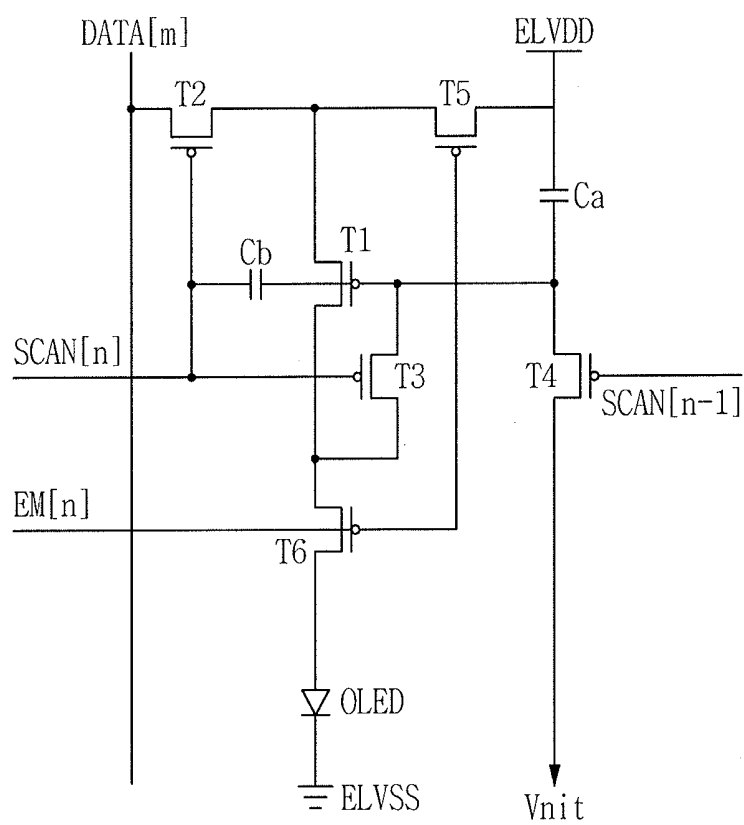


FIG. 9

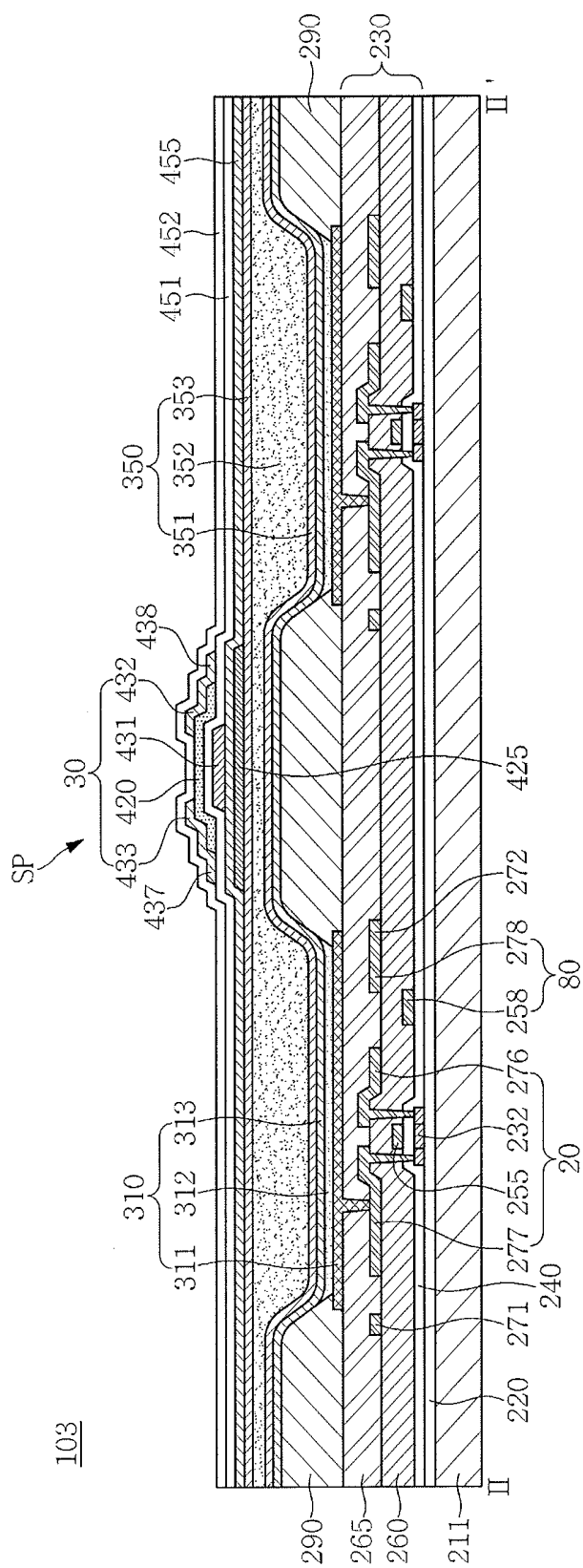


FIG. 10

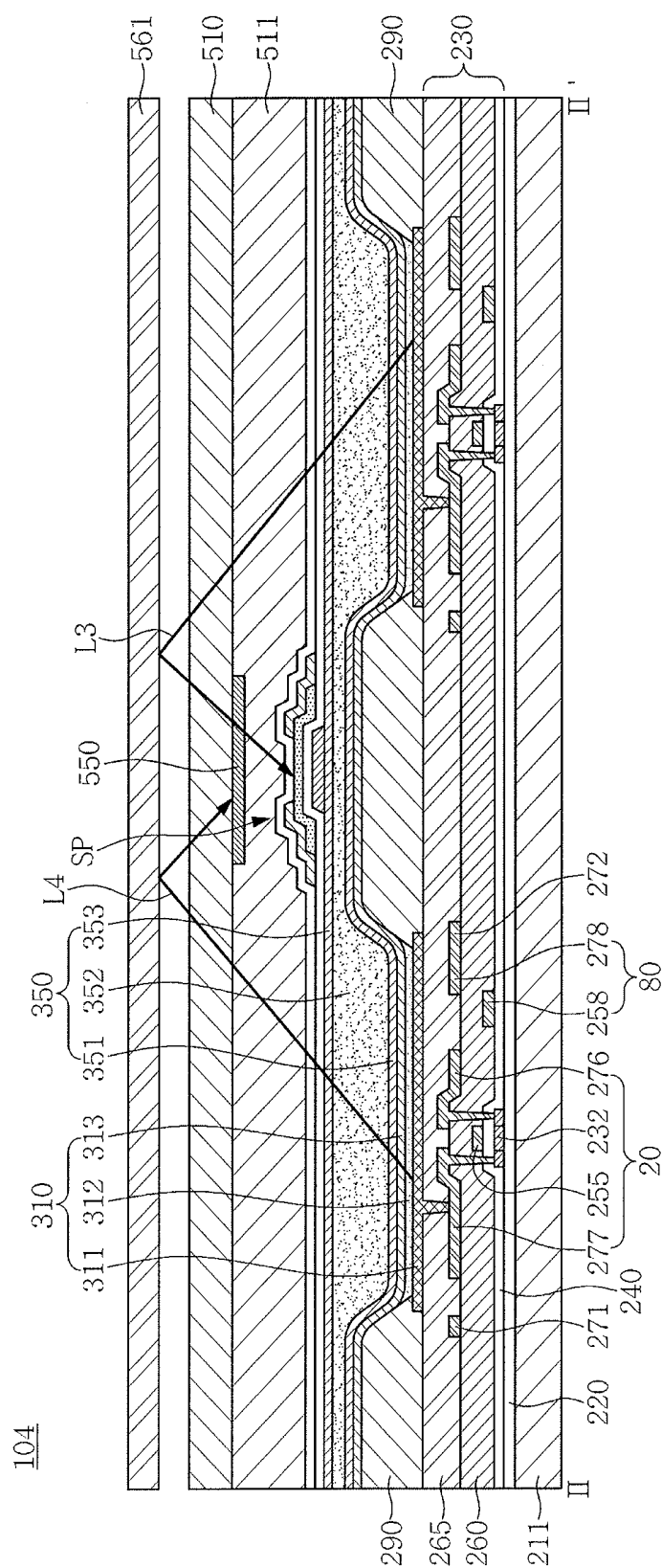
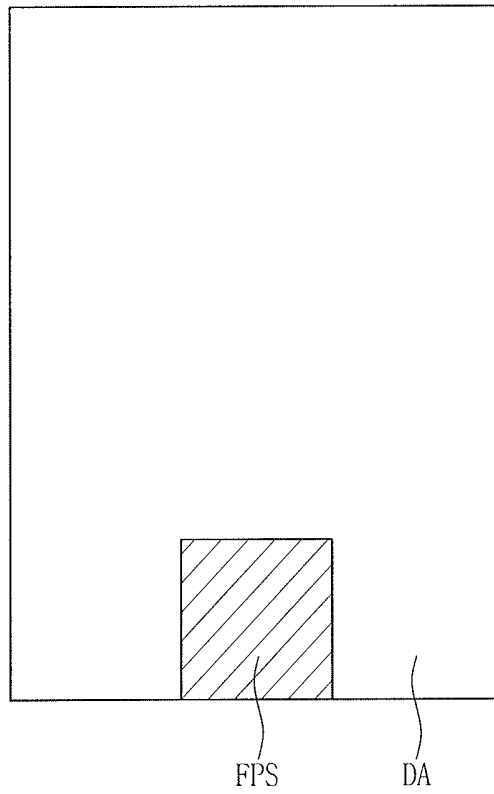


FIG. 11

105



ORGANIC LIGHT EMITTING DIODE DISPLAY DEVICE

CROSS-REFERENCE TO RELATED APPLICATION

Korean Patent Application No. 10-2016-0115055, filed on Sep. 7, 2016, in the Korean Intellectual Property Office, and entitled: "Organic Light Emitting Diode Display Device," is incorporated by reference herein in its entirety.

BACKGROUND

1. Field

Embodiments relate to an organic light emitting diode ("OLED") display device.

2. Description of the Related Art

An organic light emitting diode ("OLED") display device is a self-luminous display device that displays an image using an OLED emitting light. An OLED display device does not require a separate light source and thus may have a relatively small thickness and weight. Further, OLED display devices are garnering attention as next generation display devices for portable electronic devices because they have high quality characteristics such as low power consumption, high luminance, and high reaction speed.

The above information disclosed in this Background section is only for enhancement of understanding of the background of the inventive concept, and, therefore, it may contain information that does not form the prior art that is already known in this country to a person of ordinary skill in the art.

SUMMARY

Embodiments are directed to an organic light emitting diode display device, including a substrate, a plurality of organic light emitting diodes on the substrate, a thin film encapsulation layer on the organic light emitting diodes, and at least one sensor on the thin film encapsulation layer, the sensor including a sensing gate electrode, an oxide semiconductor layer overlapping the sensing gate electrode, a sensing source electrode connected to the oxide semiconductor layer, and a sensing drain electrode spaced apart from the sensing source electrode and connected to the oxide semiconductor layer.

The sensor may be between adjacent organic light emitting diodes.

The organic light emitting diode may include a first electrode, an organic light emitting layer on the first electrode, and a second electrode on the organic light emitting layer. The sensing gate electrode may be spaced apart from the first electrode in a lateral direction.

The organic light emitting diode display device may further include a pixel defining layer between the first electrodes, the sensor vertically overlapping the pixel defining layer.

The oxide semiconductor layer may include at least one of: zinc oxide (ZnO), zinc-tin oxide (ZTO), zinc-indium oxide (ZIO), indium oxide (InO), titanium oxide (TiO), indium-gallium-zinc oxide (IGZO), and indium-zinc-tin oxide (IZTO).

The oxide semiconductor layer may have photoreactivity. The oxide semiconductor layer may absorb a visible light.

The visible light may change an electric charge mobility of the oxide semiconductor layer.

The oxide semiconductor layer may have an electric charge mobility varying according to a wavelength of the visible light.

The oxide semiconductor layer may have thermal sensitivity.

The oxide semiconductor layer may absorb infrared light, and the infrared light may change an electric charge mobility of the oxide semiconductor layer.

The organic light emitting diode may be connected to a thin film transistor, the thin film transistor may be connected to a gate line on the substrate and a data line on the substrate, the data line intersecting the gate line, the sensing gate electrode may be connected to a reset line parallel to one of the gate line and the data line, and the sensing source electrode may be connected to a sensor power line parallel to another of the gate line and the data line.

The sensing drain electrode may be connected to an output line parallel to one of the gate line and the data line.

The organic light emitting diode display device may further include a light blocking layer between the thin film encapsulation layer and the sensor.

The organic light emitting diode display device may further include a color filter on the sensor.

The sensor may be a fingerprint recognition sensor.

The thin film encapsulation layer may include a laminate of inorganic and organic layers, the inorganic and organic layers being interposed between the oxide semiconductor layer and an upper electrode of the organic light emitting diode.

Embodiments are also directed to an organic light emitting diode device, including a substrate, a plurality of organic light emitting diodes on the substrate, a thin film encapsulation layer on the organic light emitting diodes, and a fingerprint recognition sensor on the thin film encapsulation layer, the fingerprint recognition sensor including at least one sensor that includes a sensing gate electrode, an oxide semiconductor layer overlapping the sensing gate electrode, a sensing source electrode connected to the oxide semiconductor layer, and a sensing drain electrode spaced apart from the sensing source electrode and connected to the oxide semiconductor layer.

The organic light emitting diode display device may further include a fingerprint recognition storage storing a fingerprint information of a user.

The fingerprint recognition sensor may be on the thin film encapsulation layer.

The organic light emitting diode display device may further include a pixel defining layer between the organic light emitting diodes, the sensor vertically overlapping the pixel defining layer.

BRIEF DESCRIPTION OF THE DRAWINGS

Features will become apparent to those of skill in the art by describing in detail example embodiments with reference to the attached drawings in which:

FIG. 1 illustrates a plan view of an organic light emitting diode ("OLED") display device according to a first example embodiment;

FIG. 2 illustrates a circuit diagram of a pixel and a sensor illustrated in FIG. 1;

FIG. 3 illustrates a plan view of the pixel and the sensor illustrated in FIG. 1;

FIG. 4 illustrates a cross-sectional view taken along line II-II' of FIG. 3;

FIG. 5 illustrates a cross-sectional view taken along line I-I' of FIG. 1;

FIG. 6 illustrates a cross-sectional view illustrating a touch input;

FIG. 7 illustrates a plan view of a pixel of an OLED display device according to a second example embodiment;

FIG. 8 illustrates a circuit diagram of one pixel in FIG. 7;

FIG. 9 illustrates a cross-sectional view of an OLED display device according to a third example embodiment;

FIG. 10 illustrates a cross-sectional view of an OLED display device according to a fourth example embodiment; and

FIG. 11 illustrates a plan view of an OLED display device according to a fifth example embodiment.

DETAILED DESCRIPTION

Example embodiments will now be described more fully hereinafter with reference to the accompanying drawings; however, they may be embodied in different forms and should not be construed as limited to the embodiments set forth herein. Rather, these embodiments are provided so that this disclosure will be thorough and complete, and will fully convey example implementations to those skilled in the art. In the drawing figures, the dimensions of layers and regions may be exaggerated for clarity of illustration. Like reference numerals refer to like elements throughout.

When a layer, area, or plate is referred to as being “on” another layer, area, or plate, it may be directly on the other layer, area, or plate, or intervening layers, areas, or plates may be present therebetween. Conversely, when a layer, area, or plate is referred to as being “directly on” another layer, area, or plate, intervening layers, areas, or plates may be absent therebetween. Further when a layer, area, or plate is referred to as being “below” another layer, area, or plate, it may be directly below the other layer, area, or plate, or intervening layers, areas, or plates may be present therebetween. Conversely, when a layer, area, or plate is referred to as being “directly below” another layer, area, or plate, intervening layers, areas, or plates may be absent therebetween.

The spatially relative terms “below”, “beneath”, “less”, “above”, “upper”, and the like, may be used herein for ease of description to describe the relations between one element or component and another element or component as illustrated in the drawings. It will be understood that the spatially relative terms are intended to encompass different orientations of the device in use or operation, in addition to the orientation depicted in the drawings. For example, in the case where a device shown in the drawing is turned over, the device positioned “below” or “beneath” another device may be placed “above” another device. Accordingly, the illustrative term “below” may include both the lower and upper positions. The device may also be oriented in the other direction, and thus the spatially relative terms may be interpreted differently depending on the orientations.

Throughout the specification, when an element is referred to as being “connected” to another element, the element is “directly connected” to the other element, or “electrically connected” to the other element with one or more intervening elements interposed therebetween. It will be further understood that the terms “comprises,” “comprising,” “includes” and/or “including,” when used in this specification, specify the presence of stated features, integers, steps, operations, elements, and/or components, but do not pre-

clude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof.

It will be understood that, although the terms “first,” “second,” “third,” and the like may be used herein to describe various elements, these elements should not be limited by these terms. These terms are only used to distinguish one element from another element. Thus, “a first element” discussed below could be termed “a second element” or “a third element,” and “a second element” and “a third element” can be termed likewise without departing from the teachings herein.

Unless otherwise defined, all terms used herein (including technical and scientific terms) have the same meaning as commonly understood by those skilled in the art to which this invention pertains. It will be further understood that terms, such as those defined in commonly used dictionaries, should be interpreted as having a meaning that is consistent with their meaning in the context of the relevant art and will not be interpreted in an ideal or excessively formal sense unless clearly defined in the present specification.

Hereinafter, a first example embodiment will be described with reference to FIGS. 1, 2, 3, and 4.

As illustrated in FIG. 1, an organic light emitting diode (“OLED”) display device **101** according to the first example embodiment includes a pixel PX and a sensor SP at a display area DA. Each of a plurality of the pixels PX includes an OLED **310**. Sensors SP may be disposed among the plurality of pixels PX on a plane. The sensors SP may be arranged in a selective manner. For example, the sensors SP may be disposed only at a part of the display area DA.

The OLED display device **101** may include light emission drivers **911** and **912** connected to the pixels PX to drive the pixels PX, and includes sensor drivers **921** and **922** connected to the sensors SP to drive the sensors SP. The light emission drivers may include a first light emission driver **911** applying data signals to the pixels PX, and may include a second light emission driver **912** applying gate signals to the pixels PX. The sensor drivers may include a first sensor driver **921** receiving detection signals from the sensors SP, and may include a second sensor driver **922** applying reset signals to the sensors SP. The second light emission driver **912** and the second sensor driver **922** may be disposed, for example, at a non-display area NDA of a substrate **211**, as shown in to FIG. 1.

In addition, the OLED display device **101** may include a light emission control **910** configured to control the light emission drivers **911** and **912**, a sensing control **920** configured to control the sensor drivers **921** and **922**, and a main control **900** connected to the sensing control **920**.

The light emission control **910** may control the first light emission driver **911** and the second light emission driver **912**. The light emission control **910** may include an image processing circuit or the like configured to process an image.

The sensing control **920** may control the first sensor driver **921** and the second sensor driver **922**, and may interpret the detection signal transmitted from the first sensor driver **921**.

The main control **900** may include a central processing (CPU) configured to perform various kinds of arithmetic processing, an arithmetic circuit for image processing, a memory circuit, and the like.

In other implementations, the configurations and roles of each of the drivers **911**, **912**, **921**, and **922** and the controls **910**, **920**, and **900** may be variously modified.

The sensor SP according to the first example embodiment may sense light and may operate as a touch sensor. For example, a difference in current according to a difference in

an amount of light an oxide semiconductor layer has received may be detected so that whether or not a touch action is performed on a corresponding area may be identified.

An information input process and an information output process of the OLED display device **101** will be described below.

The sensor SP may convert light incident thereto into an electric signal and transmit the electric signal to the first sensor driver **921**. The sensing control **920** may interpret the detection signal transmitted to the first sensor driver **921** to determine a selected position. The main control **900** may transmit a signal to the light emission control **910** based on an information, interpreted by the sensing control **920**, for example, an information that a predetermined icon on the screen has been selected. The emission control **910** may transmit the signal to the light emission drivers **911** and **912**, and the light emission drivers **911** and **912** may transmit an image signal to each pixel PX, which emit light according to the image signal applied thereto, thus displaying an image.

In the present example embodiment, referring to FIG. **2**, the pixel PX may include an OLED **310** and a plurality of light emission thin film transistors ("TFTs") **10** and **20**, and the sensor SP may include a sensing TFT **30**.

The OLED display device **101** may include a gate line **251**, a data line **271**, a light emission power line **272**, a sensor power line **438**, a reset line **436**, an output line **437**, and the like.

Hereinafter, the pixel PX and the sensor SP will be described in detail with reference to FIGS. **2** and **3**.

According to the first example embodiment, the pixel PX has a 2Tr-1Cap structure including the OLED **310**, a switching TFT **10**, a driving TFT **20**, and a capacitor **80**. In other implementations, the pixel PX may include three or more light emission TFTs and two or more light emission capacitors.

The light emission TFTs and the light emission capacitor may constitute a compensation circuit. The compensation circuit may improve uniformity of pixels PX in respective pixel areas, which may substantially suppress deviations in image quality. In general, the compensation circuit may include two to eight TFTs.

In FIG. **2**, the sensor SP includes one sensing TFT **30** but the sensor SP may include, for example, two or more sensing TFTs, and may further include a photosensor.

The sensing TFT **30** may include a sensing gate electrode **431**, an oxide semiconductor layer **420**, a sensing source electrode **432**, and a sensing drain electrode **433**, and the oxide semiconductor layer **420** may have photoelectric conversion characteristics.

In the present example embodiment, the sensing gate electrode **431** of the sensing TFT **30** is connected to the reset line **436**, the sensing source electrode **432** is connected to the sensor power line **438**, and the sensing drain electrode **433** is connected to the output line **437**.

In an example embodiment, by a signal of the reset line **436**, the sensing TFT **30** connected to the reset line **436** is selected to be turned on. In such an example embodiment, upon irradiation of light to the oxide semiconductor layer **420**, a current may vary. For example, a current flowing through the oxide semiconductor layer **420** varies between cases where light is irradiated and where light is not irradiated. Based on the difference in current, whether or not the oxide semiconductor layer **420** is irradiated with light may be identified. In addition, an amount of current variation may be proportional to an intensity of light irradiated to the oxide semiconductor layer **420**. Accordingly, the intensity of

light may be identified based on the amount of current variation. For example, when a user touches a screen, an intensity of a light the oxide semiconductor layer **420** receives may vary. Accordingly, a difference in current according to a difference in an amount of light the oxide semiconductor layer **420** has received may be detected so that whether or not a touch action is performed on a corresponding area may be identified.

The configurations of the pixel PX and the sensor SP may be variously modified.

With the above-described configuration, the OLED display device **101** may simultaneously display and input information, using the pixel PX and the sensor SP. In addition, according to the first example embodiment, one sensing TFT **30** may constitute one sensor SP. Accordingly, the OLED display device **101** according to the first example embodiment may achieve improved performance while having a relatively simple structure.

Hereinafter, the OLED display device **101** will be described in detail with reference to FIGS. **3** and **4**, focusing on a stacked structure.

FIG. **3** is a plan view illustrating the OLED display device **101** according to the first example embodiment, and FIG. **4** is a cross-sectional view taken along line II-II' of FIG. **3**.

The OLED display device **101** according to the first example embodiment may include the substrate **211**, a pixel circuit **230**, and the OLED **310**.

The substrate **211** may include, for example, an insulating material selected from the group of glass, quartz, ceramic, plastic, and the like. In addition, the substrate **211** may include a polymer film.

A buffer layer **220** may be disposed on the substrate **211**. The buffer layer **220** may include, for example, one or more layers selected from various inorganic layers and organic layers.

The pixel circuit **230** may be disposed on the buffer layer **220**. The pixel circuit **230** may include a plurality of TFTs **10** and **20** and drive the OLED **310**. For example, the OLED **310** may emit light according to a driving signal applied from the pixel circuit **230** to display an image.

FIGS. **3** and **4** illustrate an active matrix-type organic light emitting diode (AMOLED) display device **101** having a 2Tr-1Cap structure. For example, the 2Tr-1Cap structure may include two TFTs, e.g., a switching TFT **10** and a driving TFT **20**, and one capacitor **80** in each pixel, but the OLED display device **101** may include, for example, three or more TFTs and two or more capacitors in each pixel, and may further include additional wirings. Herein, the term "pixel" refers to a smallest element for displaying an image, and the OLED display device **101** displays an image using a plurality of pixels.

Each pixel may include the switching TFT **10**, the driving TFT **20**, the capacitor **80**, and the OLED **310**. The gate line **251** extending along one direction, and the data line **271** and the light emission power line **272** insulated from and intersecting the gate line **251** may be disposed at the pixel circuit **230**. Each pixel may be defined by the gate line **251**, the data line **271**, and the light emission power line **272** as a boundary, but the pixels may be defined by, for example, a pixel defining layer **290** or a black matrix.

The OLED **310** may include a first electrode **311**, an organic light emitting layer **312** on the first electrode **311**, and a second electrode **313** on the organic light emitting layer **312**. The organic light emitting layer **312** may include a low molecular weight organic material or a high molecular weight organic material. Holes and electrons may be applied from the first electrode **311** and the second electrode **313**,

respectively, into the organic light emitting layer **312** and then combined with each other therein to form an exciton. The OLED **310** may emit light by energy generated when the exciton falls from an excited state to a ground state.

The capacitor **80** may include a pair of capacitor plates **258** and **278**, and an insulating interlayer **260** interposed therebetween. In such an example embodiment, the insulating interlayer **260** may be a dielectric element. A capacitance of the capacitor **80** is determined by electric charges accumulated in the capacitor **80** and a voltage across the pair of capacitor plates **258** and **278**.

The switching TFT **10** may include a switching semiconductor layer **231**, a switching gate electrode **252**, a switching source electrode **273**, and a switching drain electrode **274**. The driving TFT **20** may include a driving semiconductor layer **232**, a driving gate electrode **255**, a driving source electrode **276**, and a driving drain electrode **277**. A gate insulating layer **240** may be further provided to insulate the semiconductor layers **231** and **232** and the gate electrodes **252** and **255**.

The switching TFT **10** may function as a switching element which selects a pixel to perform light emission. In the present example embodiment, the switching gate electrode **252** is connected to the gate line **251**, and the switching source electrode **273** is connected to the data line **271**. The switching drain electrode **274** is spaced apart from the switching source electrode **273** and connected to one of the capacitor plates, e.g., the capacitor plate **258**.

In the present example embodiment, the driving TFT **20** applies a driving power, which allows the organic light emitting layer **312** of the OLED **310** in a selected pixel to emit light, to the first electrode **311** which is a pixel electrode. The driving gate electrode **255** is connected to the capacitor plate **258** that is connected to the switching drain electrode **274**. Each of the driving source electrode **276** and the other of the capacitor plates, e.g., the capacitor plate **278**, is connected to the light emission power line **272**. The driving drain electrode **277** is connected to the first electrode **311** of the OLED **310** through a contact hole defined in a planarization layer **265**.

With the above-described structure, the switching TFT **10** is operated based on a gate voltage applied to the gate line **251** and serves to transmit a data voltage applied to the data line **271** to the driving TFT **20**. A voltage equivalent to a difference between a common voltage applied to the driving TFT **20** from the light emission power line **272** and the data voltage transmitted by (or from) the switching TFT **10** is stored in the capacitor **80**, and a current corresponding to the voltage stored in the capacitor **80** flows to the OLED **310** through the driving TFT **20** such that the OLED **310** may emit light.

According to the first example embodiment, the first electrode **311** is an anode.

The first electrode **311** may be a transmissive electrode having light transmittance or a reflective electrode having light reflectivity. The second electrode **313** may include a semi-transmissive layer or a reflective layer.

According to the first example embodiment, the first electrode **311** is a reflective electrode, and the second electrode **313** is a semi-transmissive electrode. A light generated in the organic light emitting layer **312** may pass through the second electrode **313** to be emitted outwards.

One or more a hole injection layer HIL or a hole transporting layer HTL may be disposed between the first electrode **311** and the organic light emitting layer **312**, and one or more of an electron transporting layer ETL or an electron injection layer EIL may be disposed between the organic

light emitting layer **312** and the second electrode **313**. The organic light emitting layer **312**, the hole injection layer HIL, the hole transporting layer HTL, the electron transporting layer ETL, and the electron injection layer EIL may each include an organic material, and thus may be referred to as an organic layer.

In the present example embodiment, the pixel defining layer **290** has an aperture. The aperture of the pixel defining layer **290** exposes a portion of the first electrode **311**. The organic light emitting layer **312** and the second electrode **313** are sequentially stacked on the first electrode **311** at the aperture of the pixel defining layer **290**. In such an example embodiment, the second electrode **213** may also be disposed on the pixel defining layer **290** as well as on the organic light emitting layer **312**. In addition, the HIL, the HTL, the ETL, and the EIL may also be disposed between the pixel defining layer **290** and the second electrode **313**. The OLED **310** emits light from the organic light emitting layer **312** in the aperture of the pixel defining layer **290**. As such, the pixel defining layer **290** may define a light emission area.

A capping layer may be disposed on the second electrode **313** to protect the OLED **310** from the external environment.

According to the first example embodiment, a thin film encapsulation layer **350** is disposed on the OLED **310**. In more detail, the thin film encapsulation layer **350** is disposed on the second electrode **313**. The thin film encapsulation layer **350** may include at least one inorganic layer **351** and **353** and at least one organic layer **352** to prevent external air, such as moisture or oxygen, from permeating into the OLED **310**. The thin film encapsulation layer **350** may have a structure in which at least one inorganic layer **351** and **353** and at least one organic layer **352** are alternately stacked. In FIG. 1, the thin film encapsulation layer **350** includes two inorganic layers **351** and **353** and one organic layer **352**, but other numbers of layers may be used.

Each of the inorganic layers **351** and **353** may include one or more inorganic materials selected from the group of: Al_2O_3 , TiO_2 , ZrO , SiO_2 , AlON , AlN , SiON , Si_3N_4 , ZnO , and Ta_2O_5 . The inorganic layers **351** and **353** may be formed through methods such as, for example, a chemical vapor deposition (CVD) method or an atomic layer deposition (ALD) method.

The organic layer **352** may include a polymer-based material. Examples of the polymer-based material may include, for example, an acrylic resin, an epoxy resin, polyimide, and polyethylene. In addition, the organic layer **352** may be formed through a thermal deposition process. The thermal deposition process for forming the organic layer **352** may be performed at a temperature range that may not damage the OLED **310**.

The inorganic layers **351** and **353** which have a high density of thin film may prevent or efficiently reduce infiltration of, mostly, moisture or oxygen. Infiltration of moisture and oxygen into the OLED **310** may be largely prevented by the inorganic layers **351** and **353**. Moisture and oxygen that have passed through the inorganic layers **351** and **353** may further be blocked by the organic layer **352**. The organic layer **352** may have relatively low moisture-infiltration preventing effect, as compared to the inorganic layers **351** and **353**. However, the organic layer **352** may also serve as a buffer layer to reduce stress among respective ones of the inorganic layers **351** and **353** and the organic layer **352**, in addition to the moisture-infiltration preventing function. Further, since the organic layer **352** has planarization characteristics, an uppermost surface of the thin film encapsulation layer **350** may be planarized by the organic layer **352**.

The thin film encapsulation layer 350 may have a thickness of, for example, about 10 μm or less. Accordingly, the OLED display device 101 may also have a significantly small thickness. By applying the thin film encapsulation layer 350 in such a manner, the OLED display device 101 may have flexible characteristics.

The sensing TFT 30 may be disposed on the thin film encapsulation layer 350. One sensing TFT 30 may constitute one sensor SP.

Referring to FIGS. 3 and 4, the reset line 436 and the sensing gate electrode 431 protruding from the reset line 436 are disposed on the thin film encapsulation layer 350. The reset line 436 may be disposed parallel to one of the gate line 251 and the data line 271 connected to the TFTs 10 and 20 of the OLED 310. Referring to FIG. 3, the reset line 436 is parallel to the gate line 251 of the OLED 310.

In the present example embodiment, the sensing gate electrode 431 does not overlap the first electrode 311 in order not to interfere with emission of light generated in the OLED 310. For example, the sensing gate electrode 431 is spaced apart from the first electrode 311 on a plane.

In the present example embodiment, the sensor SP is disposed among the OLEDs 310 on a plane. Referring to FIGS. 3 and 4, the pixel defining layer 290 is disposed between the first electrodes 311, and the sensor SP is disposed on the pixel defining layer 290.

According to the first example embodiment, the sensing gate electrode 431 is disposed on the pixel defining layer 290. Accordingly, the sensor SP is formed on the pixel defining layer 290 such that an aperture ratio of the OLED display device 101 is not reduced.

A first insulating layer 451 is disposed on the reset line 436 and the sensing gate electrode 431. The first insulating layer 451 has light transmittance and may be disposed over an entire surface of the thin film encapsulation layer 350.

The oxide semiconductor layer 420 is disposed on the first insulating layer 451. The oxide semiconductor layer 420 includes an oxide semiconductor. Examples of the oxide semiconductor may include, for example, oxides based on zinc (Zn), indium (In), gallium (Ga), tin (Sn), titanium (Ti), and alloys thereof. The oxide semiconductor layer 420 may include at least one of zinc oxide (ZnO), zinc-tin oxide (ZTO), zinc-indium oxide (ZIO), indium oxide (InO), titanium oxide (TiO), indium-gallium-zinc oxide (IGZO), and indium-zinc-tin oxide (IZTO).

Further, the sensor power line 438 and the output line 437 are disposed on the first insulating layer 451. The sensor power line 438 may be disposed parallel to one of the gate line 251 and the data line 271 connected to the TFTs 10 and 20 of the OLED 310. Referring to FIG. 3, the sensor power line 438 is parallel to the light emission power line 272 and the output line 437 is parallel to the data line 271.

The sensor power line 438 and the output line 437 do not overlap the first electrode 311 in order not to interfere with emission of light generated in the OLED 310. For example, the sensor power line 438 and the output line 437 are spaced apart from the first electrode 311 on a plane.

The sensing source electrode 432 extending from the sensor power line 438 partially overlaps the oxide semiconductor layer 420 and the sensing drain electrode 433 extending from the output line 437 partially overlaps the oxide semiconductor layer 420. The sensing source electrode 432 and the sensing drain electrode 433 are spaced apart from each other, and a portion of the oxide semiconductor layer 420 is exposed between the sensing source electrode 432 and the sensing drain electrode 433. An external stimulus

such as light is transmitted to the sensor SP through the exposed portion of the oxide semiconductor layer 420.

In addition, a second insulating layer 452 is disposed over an entire surface of the thin film encapsulation layer 350 including the sensing source electrode 432, the sensing drain electrode 433, and the exposed portion of the oxide semiconductor layer 420. The second insulating layer 452 has light transmittance.

The oxide semiconductor layer 420 may have photoreactivity. For example, the oxide semiconductor layer 420 may absorb visible light. The visible light may change electric charge mobility of the oxide semiconductor layer 420. In such an example embodiment, whether or not the sensing TFT 30 is irradiated with light may be identified by measuring a change in current flowing through the sensing TFT 30.

In an implementation, the oxide semiconductor layer 420 may have an electric charge mobility that varies depending on the wavelength of visible light.

The oxide semiconductor layer 420 may have thermal sensitivity. For example, the oxide semiconductor layer 420 may absorb infrared light, and the infrared light may change the electric charge mobility of the oxide semiconductor layer 420.

According to the first example embodiment, one sensing TFT 30 may constitute one sensor SP. Thus, the OLED display device 101 may have a relatively simple structure.

FIG. 5 is a cross-sectional view taken along line I-I' of FIG. 1.

In detail, FIG. 5 illustrates an edge of the substrate 211. Referring to FIG. 5, the second electrode 313 of the OLED 310 extends to the non-display area NDA of the substrate 211 to be connected to a common voltage wiring 315. Accordingly, a common voltage is applied to the second electrode 313.

In the present example embodiment, the thin film encapsulation layer 350 extends to the non-display area NDA to cover the second electrode 313 and the common voltage wiring 315. The organic layer 352 of the thin film encapsulation layer 350 does not extend to an end of the substrate 211 and the two inorganic layers 351 and 353 contact each other at an edge of the substrate 211. The two inorganic layers 351 and 353 contact each other, thus forming an end of the thin film encapsulation layer 350.

The output line 437 connected to the sensing drain electrode 433 is disposed on the inorganic layer 353 of the thin film encapsulation layer 350 and extends to the non-display area NDA of the substrate 211. The output line 437 is connected to an output pad 439. The output pad 439 is disposed at an end portion of the thin film encapsulation layer 350 formed by the two inorganic layers 351 and 353 in contact with each other. The output line 437 and the output pad 439 may be manufactured through substantially a same process using substantially a same material.

The output line 437 is connected to the first sensor driving 921 through the output pad 439. The first sensor driving 921 is not directly formed on the substrate 211 but may be provided in the form of a flexible printed circuit board ("FPCB") to be connected to the output pad 439 extending from the output line 437. In another implementation, the first sensor driving 921 may be formed directly on the substrate 211.

FIG. 6 is a cross-sectional view illustrating a touch input.

The sensing TFT 30 according to the first example embodiment may serve as a touch sensor.

In the example embodiment shown in FIG. 6, the second insulating layer 452 is disposed on the sensor SP including

the sensing TFT 30, a buffer layer 511 is disposed on the second insulating layer 452, and a window 511 is disposed on the buffer layer 511. The buffer layer 511 may include an adhesive. The buffer layer 511 including the adhesive may bond the window 510 and the second insulating layer 452.

As illustrated in FIG. 6, the OLED display device 101 may include the window 510. In such an example embodiment, a light generated in the OLED 310 is emitted through the window 510. Accordingly, a surface of the window 510 becomes a display surface.

In the case where a finger FG of a user contacts the window 510 or moves near the window 510, lights L1 and L2 emitted in the OLED 310 are reflected from the finger FG to reach the oxide semiconductor layer 420 of the sensing TFT 30.

Accordingly, a current flowing through the sensing TFT 30 changes, and based on this, the sensing control 920 and the main control 900 may determine that there is a touch input near the corresponding sensing TFT 30.

In more detail, after the sensing TFT 30 connected to the reset line 436 is selected and turned on by the signal of the reset line 436, in the case where the lights L1 or L2 are irradiated to the oxide semiconductor layer 420, the current may vary. Based on this difference in current, it may be identified that there is a touch input near the sensing TFT 30 including the oxide semiconductor layer 420.

FIG. 7 is a plan view illustrating a pixel of an OLED display device 102 according to a second example embodiment, and FIG. 8 is a circuit diagram illustrating one pixel in FIG. 7.

FIG. 7 illustrates four pixels and two sensing TFTs 30 disposed among the four pixels. Each pixel illustrated in FIGS. 7 and 8 includes a driving TFT T1, a switching TFT T2, one or more capacitors Ca and Cb, a scan line SCAN[n], a data line DATA[m], a first power line ELVDD, a second power line ELVSS, and an OLED.

In addition, additional TFTs T3, T4, T5, and T6 including an additional scan line SCAN[n-1], a light emission control line EM[n], an initialization voltage wiring Vint, and a compensation TFT T3 may further be provided in the pixel. An initialization voltage transmitted through the initialization voltage wiring Vint may serve to initialize the driving TFT.

The switching TFT T2 performs a switching operation according to a scan signal transmitted through the scan line SCAN[n]. For example, a gate electrode of the switching TFT T2 is connected to the scan line SCAN[n]. A source electrode of the switching TFT T2 is connected to the data line DATA[m]. The scan line SCAN[n] and the data line DATA[m] are formed in directions intersecting each other. A drain electrode of the switching TFT T2 is electrically connected to a source electrode of the driving TFT T1 and the first power line ELVDD.

The driving TFT T1 receives a data signal based on a switching operation of the switching TFT T2 and applies a driving current to the OLED.

A gate electrode of the driving TFT T1 is connected to one electrode of a first capacitor Ca. Another electrode of the first capacitor Ca is connected to the first power line ELVDD.

The first power line ELVDD is arranged parallel to the data line DATA[m]. A drain electrode of the driving TFT T1 is electrically connected to an anode of the OLED. A cathode of the OLED is connected to the second power line ELVSS. Accordingly, the OLED receives the driving current from the driving TFT T1 to emit light.

The OLED includes the anode injecting holes, the cathode injecting electrons, and a light emitting layer between the anode and the cathode.

Referring to FIG. 7, the sensing TFT 30 includes a sensing gate electrode 431, an oxide semiconductor layer 420, a sensing source electrode 432, and a sensing drain electrode 433. In an example embodiment, the oxide semiconductor layer 420 may have photoelectric conversion characteristics. The sensing gate electrode 431 of the sensing TFT 30 is connected to a reset line 436, the sensing source electrode 432 is connected to a sensor power line 438, and the sensing drain electrode 433 is connected to an output line 437.

The reset line 436 may be disposed parallel to one of the initialization voltage wiring Vint, the scan line SCAN[n], the additional scan line SCAN[n-1], and the light emission control line EM[n]. Referring to FIG. 7, the reset line 436 is parallel to the initialization voltage wiring Vint.

In addition, each of the output line 437 and the sensor power line 438 may be parallel to one of the data line DATA[m] and the first power line ELVDD. Referring to FIG. 7, the output line 437 and the sensor power line 438 are parallel to the data line DATA[m].

Referring to FIG. 7, the sensing TFT 30 is disposed among the OLEDs on a plane, which may minimize interference with emission of light generated in the OLED.

Hereinafter, an operation of the pixel illustrated in FIG. 7 will be described in detail with reference to FIG. 8.

First, while the TFT T4 is in an on state according to a scan signal transmitted through the additional scan line SCAN[n-1], an initialization voltage is applied to one end of the first capacitor Ca and the gate electrode of the driving TFT T1.

Next, the switching TFT T2 and the compensation TFT T3 are turned on according to a scan signal transmitted through the scan line SCAN[n]. While the switching TFT T2 and the compensation TFT T3 are in an on state, a data voltage transmitted through the data line DATA [in] is transmitted to the source electrode of the driving TFT T1, and the driving TFT T1 is in diode-connection.

In such an example embodiment, a voltage subtracted from the data voltage by a threshold voltage of the driving TFT T1 is applied to the gate electrode and the source electrode of the driving TFT T1.

Next, the TFTs T5 and T6 are turned on according to a light emission control signal transmitted through the light emission control line EM[n], and by an increase of the scan signal transmitted through the scan line SCAN[n], a voltage of the gate electrode of the driving TFT T1 is boosted.

While the two TFTs T5 and T6 are in an on state, a voltage of the first power line ELVDD is applied to the source electrode of the driving TFT T1, and a driving current based on a gate-source voltage difference flows through the driving TFT T1. The driving current is transmitted to the anode of the OLED through the TFT T6 in an on state.

FIG. 9 is a cross-sectional view illustrating an OLED display device 103 according to a third example embodiment.

The OLED display device 103 according to the third example embodiment includes a light blocking layer 425 between a thin film encapsulation layer 350 and a sensor SP. Referring to FIG. 9, the light blocking layer 425 is disposed on the thin film encapsulation layer 350, a passivation layer 455 is disposed on the light blocking layer 425, and a sensing TFT 30 is disposed on the passivation layer 455 to overlap the light blocking layer 425.

For example, the light blocking layer 425 is disposed between the thin film encapsulation layer 350 and a sensing

gate electrode **431** of the sensing TFT **30**. The light blocking layer **425** helps to prevent light generated in an OLED **310** from directly affecting an oxide semiconductor layer **420** of the sensing TFT **30**.

FIG. **10** is a cross-sectional view illustrating an OLED display device **104** according to a fourth example embodiment.

The OLED display device **104** according to the fourth example embodiment includes a color filter **550** on a sensor SP. Referring to FIG. **9**, a window **510** is disposed on the sensor SP, and the color filter **550** is disposed on the window **510**. The color filter **550** overlaps the sensor SP including a sensing TFT **30**.

The color filter **550** allows only light of a predetermined color to reach an oxide semiconductor layer **420** of the sensing TFT **30**. Accordingly, the sensor SP may sense an intensity of the predetermined color.

Referring to FIG. **10**, lights **L3** and **L4** emitted from an OLED **310** pass through the color filter **550** when they are incident to the oxide semiconductor layer **420** after being reflected by a reflection object **561**, for example, a colored object, or a finger, stylus, etc. For example, when the color filter **550** is a red color filter, a red light **L3** passes through the color filter **550** to be incident to the oxide semiconductor layer **420**. On the other hand, a light **L4** of a color other than the red color is absorbed by the color filter **550** and fails to reach the oxide semiconductor layer **420**. Accordingly, the sensor SP may sense an intensity of the red light.

For example, in the case where a plurality of sensors SP independently capable of sensing blue, red, and green colors, respectively, are disposed on a thin film encapsulation layer **350**, a color of the reflection object **561** may be identified based on integrated analysis on color intensity information obtained from each sensor SP. In the case where these sensors SP are arranged at high density, an image of the reflection object **561** may be recognized by the sensor SP.

FIG. **11** is a plan view illustrating an OLED display device **105** according to a fifth example embodiment.

The OLED display device **105** according to the fifth example embodiment has a display area DA and a fingerprint recognition sensor FPS at a portion of the display area DA.

The fingerprint recognition sensor FPS may be disposed at a portion of a thin film encapsulation layer **350** and may include a plurality of sensors SP. The sensor SP arranged for fingerprint recognition may be referred to as a fingerprint recognition sensor.

For fingerprint recognition, a main control **900** may include a fingerprint recognition storage. In addition, the sensor SP may be connected to the fingerprint recognition storage.

In addition, a fingerprint information of a predetermined user may be stored in the fingerprint recognition storage. Accordingly, whether or not a fingerprint recognized using the fingerprint recognition sensor FPS matches the fingerprint of the predetermined user may be verified. In the case where the fingerprint recognized using the fingerprint recognition sensor FPS matches the fingerprint of the predetermined user, the OLED display device **105** may be unlocked, for example.

By way of summation and review, display devices may be made to receive input of information by contact with, for example, a finger or a stylus pen and a screen. Such display devices having an information input function may be used for, for example, a mobile phone, a personal digital assistant ("PDA"), a portable game machine, a car navigation system, an automated teller machine ("ATM"), and the like. A

display device having an information input function may be manufactured by, for example, separately manufacturing a touch panel and combining it with a display panel, or by forming various sensors directly in the display panel.

As described above, embodiments relate to an OLED display device having an information display function and an information input function.

In one or more example embodiments, the OLED display device has a simple structure while having both an information display function and an information input function.

Example embodiments have been disclosed herein, and although specific terms are employed, they are used and are to be interpreted in a generic and descriptive sense only and not for purpose of limitation. In some instances, as would be apparent to one of ordinary skill in the art as of the filing of the present application, features, characteristics, and/or elements described in connection with a particular embodiment may be used singly or in combination with features, characteristics, and/or elements described in connection with other embodiments unless otherwise specifically indicated. Accordingly, it will be understood by those of skill in the art that various changes in form and details may be made without departing from the spirit and scope as set forth in the following claims.

What is claimed is:

1. An organic light emitting diode display device, comprising:

- a substrate;
- a plurality of organic light emitting diodes on the substrate;
- a thin film encapsulation layer on the organic light emitting diodes; and
- at least one sensor on the thin film encapsulation layer, the sensor including:
 - a sensing gate electrode;
 - an oxide semiconductor layer overlapping the sensing gate electrode;
 - a sensing source electrode connected to the oxide semiconductor layer; and
 - a sensing drain electrode spaced apart from the sensing source electrode and connected to the oxide semiconductor layer.

2. The organic light emitting diode display device as claimed in claim 1, wherein the sensor is between adjacent organic light emitting diodes.

3. The organic light emitting diode display device as claimed in claim 1, wherein each organic light emitting diode of the plurality of organic light emitting diodes includes:

- a first electrode;
- an organic light emitting layer on the first electrode; and
- a second electrode on the organic light emitting layer, wherein the sensing gate electrode is spaced apart from the first electrode in a lateral direction.

4. The organic light emitting diode display device as claimed in claim 3, further comprising a pixel defining layer between the first electrodes, the sensor vertically overlapping the pixel defining layer.

5. The organic light emitting diode display device as claimed in claim 1, wherein the oxide semiconductor layer includes at least one of: zinc oxide (ZnO), zinc-tin oxide (ZTO), zinc-indium oxide (ZIO), indium oxide (InO), titanium oxide (TiO), indium-gallium-zinc oxide (IGZO), and indium-zinc-tin oxide (IZTO).

6. The organic light emitting diode display device as claimed in claim 1, wherein the oxide semiconductor layer has photoreactivity.

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7. The organic light emitting diode display device as claimed in claim 1, wherein the oxide semiconductor layer absorbs a visible light.

8. The organic light emitting diode display device as claimed in claim 7, wherein the visible light changes an electric charge mobility of the oxide semiconductor layer.

9. The organic light emitting diode display device as claimed in claim 7, wherein the oxide semiconductor layer has an electric charge mobility varying according to a wavelength of the visible light.

10. The organic light emitting diode display device as claimed in claim 1, wherein the oxide semiconductor layer has thermal sensitivity.

11. The organic light emitting diode display device as claimed in claim 1, wherein the oxide semiconductor layer absorbs an infrared light, and the infrared light changes an electric charge mobility of the oxide semiconductor layer.

12. The organic light emitting diode display device as claimed in claim 1, wherein the organic light emitting diode is connected to a thin film transistor,

the thin film transistor is connected to a gate line on the substrate and a data line on the substrate, the data line intersecting the gate line,

the sensing gate electrode is connected to a reset line parallel to one of the gate line and the data line, and the sensing source electrode is connected to a sensor power line parallel to another of the gate line and the data line.

13. The organic light emitting diode display device as claimed in claim 12, wherein the sensing drain electrode is connected to an output line parallel to one of the gate line and the data line.

14. The organic light emitting diode display device as claimed in claim 1, further comprising a light blocking layer between the thin film encapsulation layer and the sensor.

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15. The organic light emitting diode display device as claimed in claim 1, further comprising a color filter on the sensor.

16. The organic light emitting diode display device as claimed in claim 1, wherein the sensor is a fingerprint recognition sensor.

17. The organic light emitting diode display device as claimed in claim 1, wherein the thin film encapsulation layer includes a laminate of inorganic and organic layers, the inorganic and organic layers being interposed between the oxide semiconductor layer and an upper electrode of the organic light emitting diode.

18. An organic light emitting diode device, comprising;
a substrate;

a plurality of organic light emitting diodes on the substrate;

a thin film encapsulation layer on the organic light emitting diodes; and

a fingerprint recognition sensor on the thin film encapsulation layer, the fingerprint recognition sensor including at least one sensor that includes:

a sensing gate electrode;

an oxide semiconductor layer overlapping the sensing gate electrode;

a sensing source electrode connected to the oxide semiconductor layer; and

a sensing drain electrode spaced apart from the sensing source electrode and connected to the oxide semiconductor layer.

19. The organic light emitting diode display device as claimed in claim 18, further comprising a fingerprint recognition storage storing a fingerprint information of a user.

20. The organic light emitting diode display device as claimed in claim 18, further comprising a pixel defining layer between the organic light emitting diodes, the sensor vertically overlapping the pixel defining layer.

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摘要(译)

一种有机发光二极管显示装置，包括基板，基板上的多个有机发光二极管，有机发光二极管上的薄膜封装层，以及薄膜封装层上的至少一个传感器，该传感器包括：感测栅电极，与感测栅电极重叠的氧化物半导体层，连接到氧化物半导体层的感测源电极，以及与感测源电极间隔开并连接到氧化物半导体层的感测漏电极。

